22151

M. E. 2nd Semester (ECE) Examination, May–2010

VLSI DESIGN

Paper–MEEC-506

Time allowed : 3 hours] *[Maximum marks : 100*

Note : *Attempt any **five** question. All questions carry equal marks.*

1. (a) Write in detail about construction and working of enhancement type NMOS transistor. 10

(b) Discuss briefly about NMOS fabrication. 10

2. Draw circuit diagram and plot VTC for a NMOS inverter with

(a) Resistive load

(b) Enhancement load

(c) Depletion load. 20

3. (a) Write in detail about various MOS transistor parameters.

(b) Draw stick diagram and layout for a CMOS inverter.

4. Derive expression for (i) Noise Margin (ii) Propagation delay for CMOS Inverter. 20

5. (a) Draw and write in detail about CMOS as a switch. 10

   (b) What are domino logic circuits ? 10

6. What are various scaling models ? Also discuss briefly about scaling of wires and interconnects. 20

7. (a) Discuss the following for MOS devices

   (i) Short Channel Effects

   (ii) Narrow Channel Effects. 14

   (b) What are clocked sequential circuits. 6

8. Write short notes on (any *two*) ;

   (i) Parallel Adders

   (ii) Pseudo NMOS logic circuits

   (iii) Lambda based design rules. 2×10